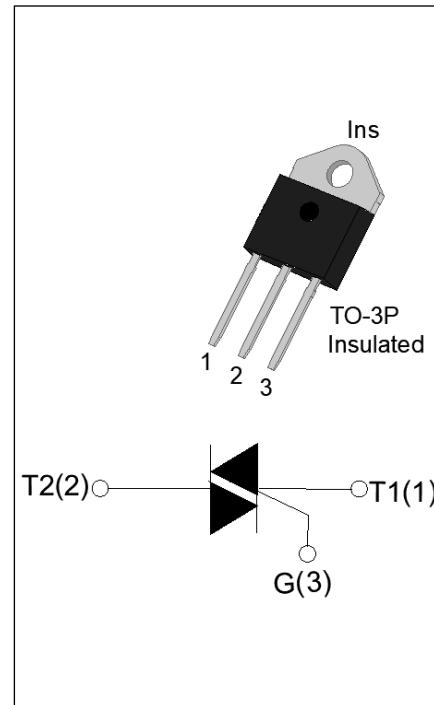


**DESCRIPTION:**

The JST41Z-600B triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. By using an internal ceramic pad, JST41Z-600B provides a rated insulation voltage of 2500 VRMS, complying with UL standards (File ref: E252906). Package TO-3P is RoHS compliant.

**MAIN FEATURES**

Symbol	Value	Unit
$I_{T(RMS)}$	40	A
$V_{DRM}/V_{RRM}$	600	V
$I_{GT\text{ I/II/III/IV}}$	50/50/50/70	mA

**ABSOLUTE MAXIMUM RATINGS**

Parameter	Symbol	Value	Unit
Storage junction temperature range	$T_{stg}$	-40-150	°C
Operating junction temperature range	$T_j$	-40-125	°C
Repetitive peak off-state voltage ( $T_j=25^\circ\text{C}$ )	$V_{DRM}$	600	V
Repetitive peak reverse voltage ( $T_j=25^\circ\text{C}$ )	$V_{RRM}$	600	V
RMS on-state current ( $T_c \leqslant 81^\circ\text{C}$ )	$I_{T(RMS)}$	40	A
Non repetitive surge peak on-state current (full cycle , $t_p=20\text{ms}$ , $T_j=25^\circ\text{C}$ )	$I_{TSM}$	420	A
Non repetitive surge peak on-state current (full cycle , $t_p=16.6\text{ms}$ , $T_j=25^\circ\text{C}$ )		462	
$I^2t$ value for fusing ( $t_p=10\text{ms}$ , $T_j=25^\circ\text{C}$ )	$I^2t$	1000	$\text{A}^2\text{s}$
Critical rate of rise of on-state current ( $I_G=2 \times I_{GT}$ , $f=100\text{Hz}$ , $T_j=125^\circ\text{C}$ )	I - II III-IV	100 50	$\text{A}/\mu\text{s}$
Peak gate current ( $t_p=20\mu\text{s}$ , $T_j=125^\circ\text{C}$ )	$I_{GM}$	8	A
Average gate power dissipation ( $T_j=125^\circ\text{C}$ )	$P_{G(AV)}$	1	W
Peak gate power	$P_{GM}$	40	W

Peak pulse voltage (T <sub>j</sub> =25°C; non-repetitive,off-state;FIG.7)	V <sub>pp</sub>	0.9	kV
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**ELECTRICAL CHARACTERISTICS (T<sub>j</sub>=25°C unless otherwise specified)**

Symbol	Test Condition	Quadrant	Value		Unit
I <sub>GT</sub>	V <sub>D</sub> =12V R <sub>L</sub> =33Ω	I - II -III	MAX.	50	mA
		IV		70	
V <sub>GT</sub>		ALL	MAX.	1.3	V
V <sub>GD</sub>	V <sub>D</sub> =V <sub>DRM</sub> T <sub>j</sub> =125°C R <sub>L</sub> =3.3KΩ	ALL	MIN.	0.2	V
I <sub>L</sub>	I <sub>G</sub> =1.2I <sub>GT</sub>	I - III-IV	MAX.	80	mA
		II		160	
I <sub>H</sub>	I <sub>T</sub> =500mA		MAX.	80	mA
dV/dt	V <sub>D</sub> =400V Gate Open T <sub>j</sub> =125°C		MIN.	1500	V/μs
(dV/dt)c	(dI/dt)c=20A/ms, T <sub>j</sub> =125°C		MIN.	20	V/μs
t <sub>on</sub>	I <sub>G</sub> =80mA I <sub>A</sub> =400mA I <sub>R</sub> =40mA T <sub>j</sub> =25°C	TYP.	10	μs	
t <sub>off</sub>			70		

**STATIC CHARACTERISTICS**

Symbol	Parameter		Value(MAX.)	Unit
V <sub>TM</sub>	I <sub>TM</sub> =60A t <sub>p</sub> =380μs	T <sub>j</sub> =25°C	1.4	V
V <sub>TO</sub>	Threshold voltage	T <sub>j</sub> =125°C	0.73	V
R <sub>D</sub>	Dynamic resistance	T <sub>j</sub> =125°C	10	mΩ
I <sub>DRM</sub>	V <sub>D</sub> =V <sub>DRM</sub> V <sub>R</sub> =V <sub>RRM</sub>	T <sub>j</sub> =25°C	5	μA
I <sub>RRM</sub>		T <sub>j</sub> =125°C	3	mA

**THERMAL RESISTANCES**

Symbol	Parameter	Value	Unit
R <sub>th(j-c)</sub>	junction to case (AC)	0.85	°C/W
R <sub>th(j-a)</sub>	junction to ambient (AC)	50	°C/W

**ORDERING INFORMATION**

<b>J</b>	<b>ST</b>	<b>41</b>	<b>Z</b>	<b>-600</b>	<b>B</b>
JieJie Microelectronics Co., Ltd.					

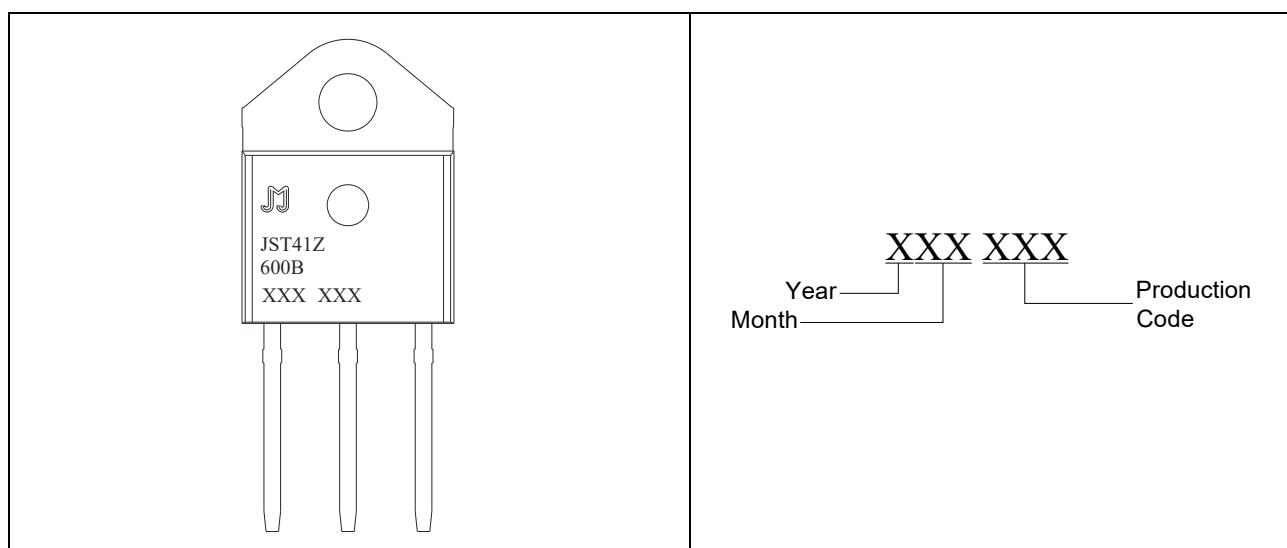
Triacs

$I_T(RMS):40A$

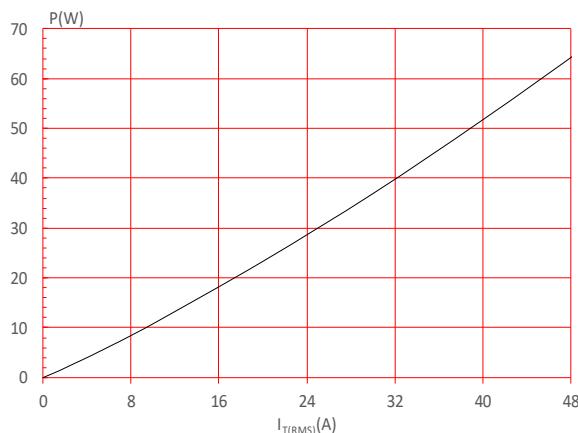
Z:TO-3P(Ins)

600: $V_{DRM}/V_{RRM} \geq 600V$

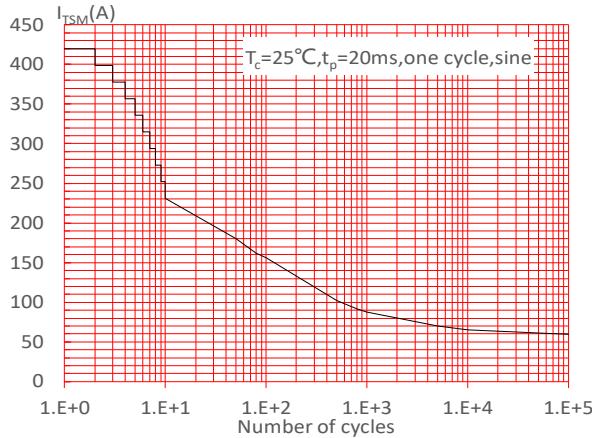
B: $I_{GT1-3} \leq 50mA$   $I_{GT4} \leq 70mA$

**MARKING**

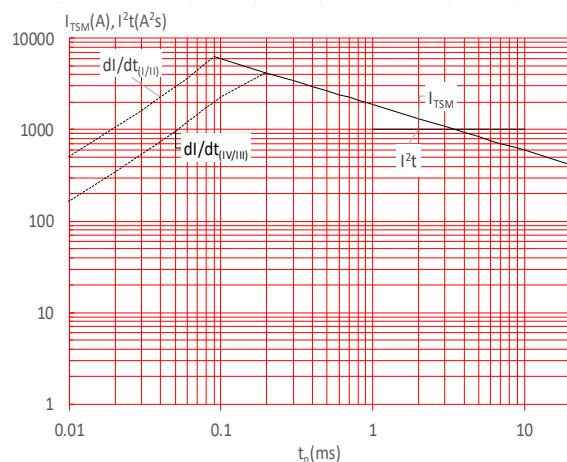
**FIG.1** Maximum power dissipation versus RMS on-state current



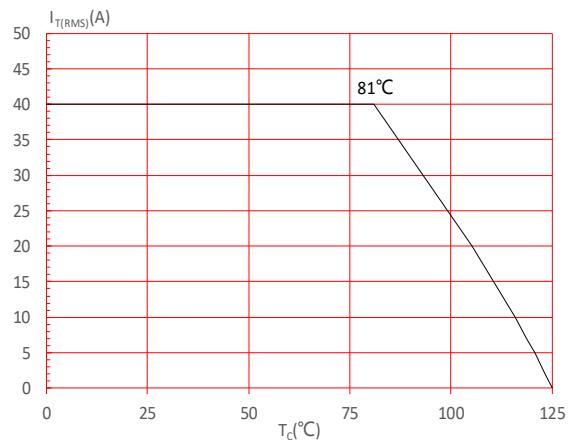
**FIG.3:** Surge peak on-state current versus number of cycles



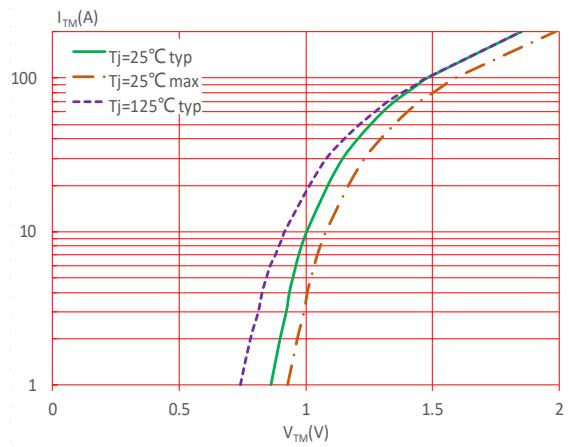
**FIG.5:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p$  <20ms, and corresponding value of  $I^2t$   
( I - II :  $dI/dt < 100A/\mu s$ ; III-IV :  $dI/dt < 50A/\mu s$ )



**FIG.2:** RMS on-state current versus case temperature



**FIG.4:** On-state characteristics



**FIG.6:** Relative variations of gate trigger current, holding current and latching current versus junction temperature

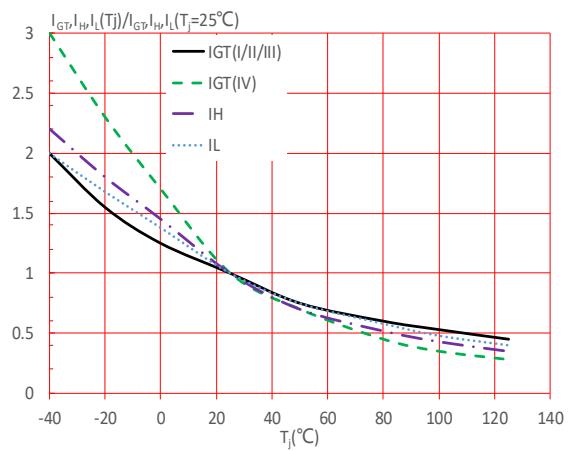
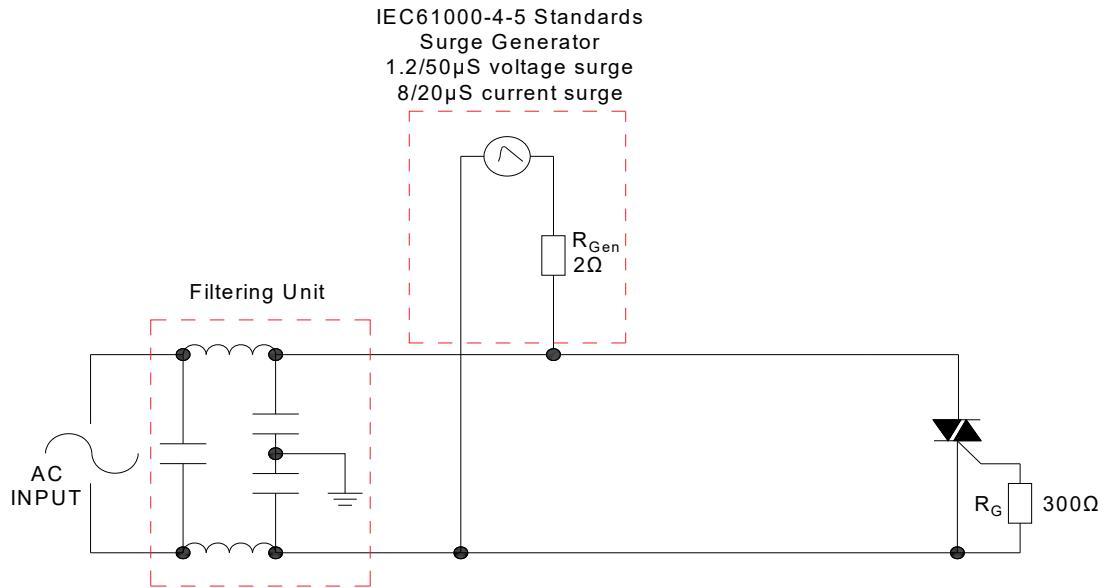


FIG.7: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



## SHAPING AND SOLDERING PARAMETERS

Refer to 《Instructions for installation of plastic-sealed in-line power devices》 released by JieJie.

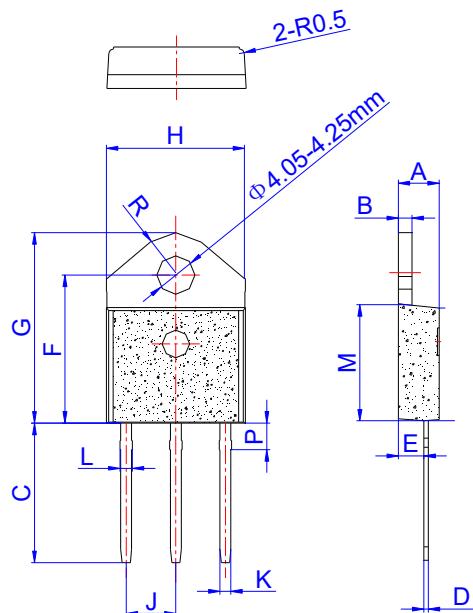
## ORDERING INFORMATION

Order code	Voltage $V_{DRM}/V_{RRM}$ (V)	IGT(mA)		Package	Base qty. (pcs)	Delivery mode
		I -II -III	IV			
JST41Z-600B	600	50	70	TO-3P(Ins)	30	Tube

## Document Revision History

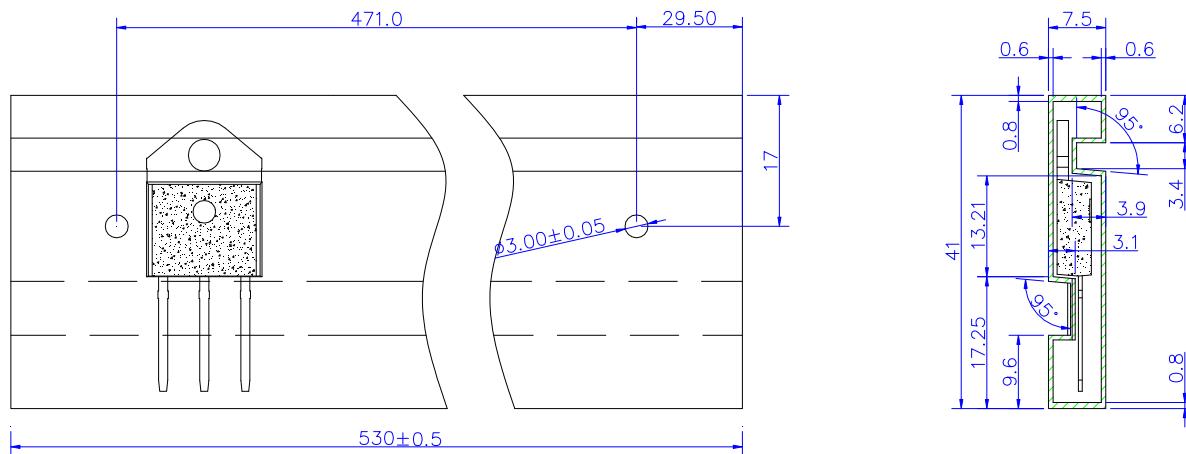
Date	Revision	Changes
Apr.14, 2023	A.1.0	Last updated

## PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	1.45		1.55	0.057		0.061
C	14.35		15.60	0.565		0.614
D	0.50		0.70	0.020		0.028
E	2.70		2.90	0.106		0.114
F	15.80		16.50	0.622		0.650
G	20.40		21.10	0.803		0.831
H	15.10		15.50	0.594		0.610
J	5.40		5.65	0.213		0.222
K	1.10		1.40	0.043		0.055
L	1.25		1.45	0.049		0.057
M	12.37		12.77	0.487		0.503
P	2.80		3.00	0.110		0.118
R		4.35			0.171	

## DELIVERY MODE



PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
TO-3P	TUBE	30	450	2,250

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